Features

- Contactless Power Supply
- Contactless Read/Write Data Transmission
- Radio Frequency f_{RF} from 100 kHz to 150 kHz
- 128-bit EEPROM User Memory: 16 Bytes (8 Bits Each)
- 8-bit Configuration Memory
- · High Q-antenna Tolerance Due to Built-in Options
- Applications
 - Access Control
 - Standard Unique Format (Manchester, RF/64)
 - 40-bitData Memory
 - 14-bit Parity Memory
 - 9-bit Header Memory
- On-chip Trimmed Antenna Capacitor
 - 330 pF ±3%
 - 250 pF ±3%
- Mega Pads 200 μ m imes 400 μ m
- Mega Pads 200 μ m imes 400 μ m with 25 μ m Gold Bumps for Direct Coil Bonding
- · Other Options:
 - Direct Access Mode
 - OTP Functionality

Description

The ATA5575 is a contactless read/write identification IC (IDIC®) for applications in the 100-kHz to 150-kHz frequency band. A single coil connected to the chip serves as the IC's power supply and bi-directional communication interface. The antenna and chip together form a transponder or tag.

The on-chip 128-bit user EEPROM (16 bytes with 8 bits each) can be read and written byte-wise from a base station (reader). Data is transmitted from the IDIC (uplink) using load modulation. This is achieved by damping the RF field with a resistive load between the two terminals Coil 1 and Coil 2. The IC receives and decodes serial base station commands (downlink), which are encoded as 100% amplitude-modulated (OOK) pulse-interval-encoded bit streams.

The ATA5575 is an EEPROM-based circuit. It is optimized for maximum read range. Programming is also possible, but the write range is limited.

The chip has to be locked after loading the application-specific data into the device. Until the enable bits are set properly, the ATA5575M1 transmits all digits "0" in unique format. Typical applications run at 125 kHz.



Read/Write LF RFID IDIC 100 kHz to 150 kHz

ATA5575M1

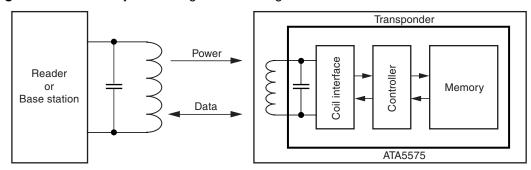
Preliminary





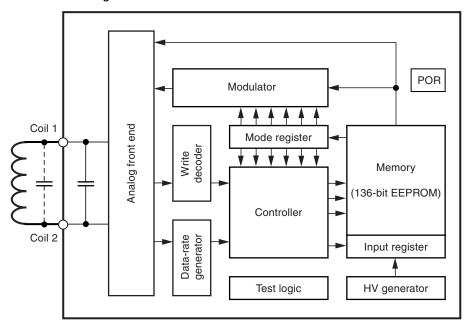
2. System Block Diagram

Figure 2-1. RFID System Using ATA5575 Tag



3. ATA5575 - Functional Blocks

Figure 3-1. Block Diagram



4. Analog Front End (AFE)

The AFE includes all circuits which are directly connected to the coil terminals, it generates the IC's power supply and handles the bi-directional data communication with the reader. The AFE consists of the following blocks:

- Rectifier to generate a DC supply voltage from the AC coil voltage
- Clock extractor
- Switchable load between Coil 1 and Coil 2 for data transmission from tag to the reader
- Field-gap detector for data transmission from the base station to the tag
- ESD protection circuitry

4.1 Data Rate Generator

The data rate is fixed to RF/64.

4.2 Write Decoder

The write decoder detects the write gaps and verifies the validity of the data stream according to the Atmel[®] downlink protocol (pulse interval encoding).

4.3 HV Generator

This on-chip charge pump circuit generates the high voltage required for programming the EEPROM.

4.4 DC Supply

Power is externally supplied to the IDIC via the two coil connections. The IC rectifies and regulates this RF source and uses it to generate its supply voltage.

4.5 Power-On Reset (POR)

The power-on reset circuit blocks the voltage supply to the IDIC until an acceptable voltage threshold has been reached. This, in turn, triggers the default initialization delay sequence. During this configuration period of 98 field clocks, the ATA5575 is initialized with the configuration data stored in EEPROM byte 16.

4.6 Clock Extraction

The clock extraction circuit uses the external RF signal as its internal clock source.

4.7 Controller

The control logic module executes the following functions:

- Load mode register with configuration data from EEPROM byte 16 after power-on and during reading
- Controls each EEPROM memory read/write access and handles the data protection
- Handle the downlink command decoding, detecting protocol violations and error conditions





4.8 Mode Register

The mode register maintains a readable shadow copy of the configuration data held in byte 16 of the EEPROM. It is continually refreshed during read mode and (re-)loaded after every POR event or reset command. Depending on the version, the configuration data is pre-programmed when leaving Atmel's production.

4.9 Modulator

The modulator encodes the serialized EEPROM data for transmission to a tag reader or a base station. Modulation available: Manchester.

4.10 Memory

Figure 4-1. Memory Map

1......8

Configuration Data

Configuration Data	Byte 16
User Data	Byte 15
User Data	Byte 14
User Data	Byte 13
User Data	Byte 12
User Data	Byte 11
User Data	Byte 10
User Data	Byte 9
User Data	Byte 8
User Data	Byte 7
User Data	Byte 6
User Data	Byte 5
User Data	Byte 4
User Data	Byte 3
User Data	Byte 2
User Data	Byte 1
User Data	Byte 0
	—

8 bits

Not transmitted

The memory is a 136-bit EEPROM, which is arranged in 17 bytes of 8 bits each. Programming is carried out byte-wise, so a complete byte will be programmed with a single command.

Byte 16 contains the mode/configuration data, which is not transmitted during regular read operations.

A special bit combination (see Table 5-1 on page 5) in byte 16 will lock the entire memory. Once locked, the memory (including byte 16 itself) can not be re-programmed once more via the RF field.

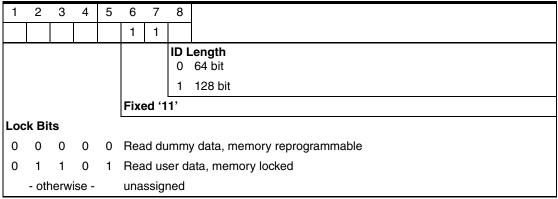
5. Operating the ATA5575M1

The ATA5575M1 is mainly designed for access control applications. The configuration register, Byte 16, enables the customer to configure the chip according to the individual application. Modulation is Manchester coding with a data bit rate of RF/64. Default ID length is 64 bit. For specific applications, the ID length can be switched to 128 bit by setting bit 8 of byte 16 to "1".

As long as the lock bits are set to '00000b' the memory is reprogrammable, however, ATA5575M1 sends out dummy data (unique format with all digits set to '0'; see also Section 7. "Programming Examples" on page 13) in regular read mode.

By setting the lock-bits to "01101" the memory is locked and can not be altered. The ATA5575M1 sends out the programmed user data in regular read mode.

Table 5-1. ATA5575M1: Byte 16 Configuration Register Mapping



Note: Bits 6 and 7 must always be set to '1', otherwise, malfunction will occur

5.1 Lock Bits

When set to '01101b', the configuration registers' lock bits prevent the entire memory from being reprogrammed. Consequently the ATA5575M1 will send the user data in regular read mode after POR has occurred.

In delivery state the lock bits are programmed to "00000b" and the device can be programmed by the customer by transmitting dummy data (unique format with all digits set to '0'; see also Section 7. "Programming Examples" on page 13) in Manchester Code with a data bit rate of RF/64.

All other combinations of bit 1- bit 5 are not defined and may lead to malfunction of the IC.





5.2 Modulation

The modulator of the ATA5575M1 is fixed to Manchester coding with a data bit rate of RF/64.

Table 5-2. ATA5575M1: Types of Modulation

Mode	Direct Data Output Encoding
Manchester	0 = falling edge, 1 = rising edge on mid-bit

5.3 ID Length

The ATA5575M1 offers different settings for various ID lengths. If bit 8 of byte 16 is set to '1' the ID length is 128 bit. Resetting bit 8 of byte 16 to '0' results in an ID length of 64 bits.

5.4 Unique Data Format and Unique ID

During Atmel's production process the ATA5575M1 is be pre-configured in unique data format and a unique ID (UID) will be stored in user data. The unique ID consists of Atmel's production information such as lot number, wafer number, and die on wafer number. With these data each chip can be traced and concurrently each chip has its own unique ID for identification purposes.

For unique data format please refer to Section 7. "Programming Examples" on page 13. Section 10.2 "ATA5575M1 Configuration on Delivery" on page 17 describes the formation of the unique ID based on Atmel's production information.

5.5 Tag-to-reader Communication (Uplink)

Immediately after entering the reader field, generating the internal supply voltage and the analog POR, the tag cycles dummy data when enable bits are not set by load modulation according to configuration setting. This resistive load modulation can be detected at the reader device. When enable bits are set, the reader device in public mode and sends its data that is stored in the EEPROM.

5.5.1 Regular Read Mode

6

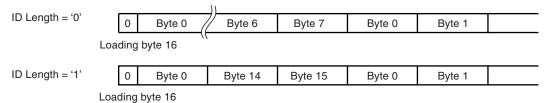
In regular read mode, data from the memory is transmitted serially, starting with byte 0, bit 1, up to the last byte, bit 8. Last byte is defined by bit 8 of byte 16, ID Length. When the last bit of the last byte (defined by ID length) has been read, data transmission restarts with byte 0, bit 1.

The last byte is 15 when ID length = 1 (128 bit).

The last byte is 7, when ID length = 0 (64 bit) has been chosen.

Each time the ATA5575 enters regular or byte read mode, the first bit transmitted is a logical '0'. The data stream starts with bit 1 of byte 0 or bit 1 of the addressed byte.

Figure 5-1. Examples for Different ID Length Settings



5.5.2 Byte Read Mode

With the direct access command, only the addressed byte is read repetitively. This mode is called byte read mode. Direct access is entered by transmitting the opcode ('10'), a single 0 bit and the requested 5-bit byte address.

Note: A direct access to bytes 18 to 31 reads all data bits as zero.

5.6 Reader-to-tag Communication (Downlink)

Data is transmitted to the tag by interrupting the RF field with short field gaps (on-off keying) according to the ATA5575's write method (downlink mode). The duration of these field gaps is, for example, 100 µs. The time between two gaps encodes the 0/1 information to be transmitted (pulse interval encoding). The time between two gaps is nominally 24 field clocks for a 0 and 56 field clocks for a 1. When there is no gap for more than 64 field clocks after a previous gap, the ATA5575 exits the downlink mode. The tag starts with the command execution if the correct number of bits were received. If a failure is detected, the ATA5575 does not continue and enters regular read mode.

The initial gap, called start gap, triggers the reader-to-tag communication. The start gap may need to be longer than the subsequent gaps - so-called write gaps - in order to be detected reliably.

A start gap will be accepted at any time after the mode register has been loaded (≥ 1 ms).

Figure 5-2. Start of Reader-to-tag Communication (Downlink)

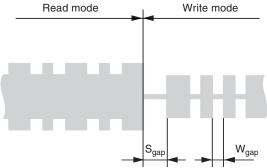


Table 5-3. Downlink Data Decoding Scheme

Parameter	Remark	Symbol	Min.	Тур.	Max.
Start gap		S_{gap}	8	15	50
Write gap		W _{gap}	8	10	20
Write data coding (gap	0 data	d ₀	18	25	33
separation)	1 data	d ₁	50	58	65

Note: All absolute times are given under the assumption of $T_C = 1/f_C = 8 \mu s$ ($f_C = 125 \text{ kHz}$)



5.6.1 Downlink Data Protocol

The ATA5575 expects to receive a dual bit opcode as a part of the reader command sequence. There are three valid opcodes:

- The opcode '10' precedes all downlink operations for writing data into the EEPROM A single '10' opcode (Read ID) leads to reading the ID
- The opcode '11' reads the upper bytes when the ID length (bit 8 of byte 16) is set to '0' If the ID length is set to '1' opcode '11' is the same as opcode '10'
- The RESET opcode '00' initiates an initialization cycle

Downlink requirements:

- The write byte requires the opcode '10', a '0' bit, 8 data bits and the 5-bit address (16 bits total)
- For direct byte access, the opcode '10', a '0' bit and a 5-bit address (8 bits total), is required Note: The data bits are read in the same order as being written.

If the transmitted command sequence is invalid, the ATA5575 enters regular read mode.

Figure 5-3. Complete Write Sequence

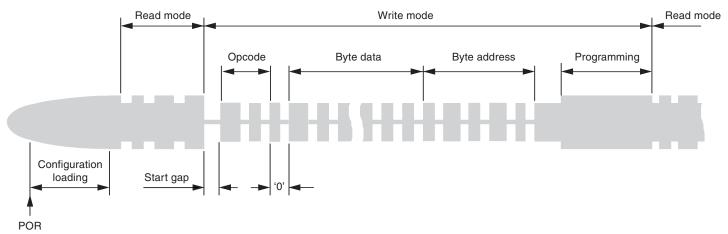
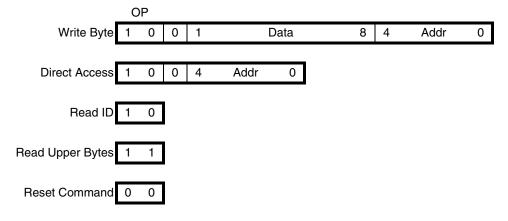


Figure 5-4. ATA5575 Command Formats



5.7 Programming

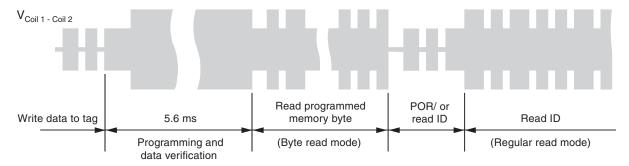
When all necessary information has been received by the ATA5575, programming may proceed. There is a clock delay between the end of the writing sequence and the start of programming.

Typical programming time is 5.6 ms. This cycle includes a data verification read to grant secure and correct programming. After successful programming, the ATA5575 enters byte read mode, transmitting the byte just programmed.

After validation of the command sequence, the new data will be programmed into the EEPROM memory.

Each programming cycle consists of four consecutive steps: erase byte, erase verification (data = 0), programming, programming verification (corresponding data bits = 1).

Figure 5-5. Coil Voltage after Programming a Byte







6. Error Handling

To prevent that invalid bits are programmed into the EEPROM, the device is able to detect two main error types and several error conditions.

6.1 Errors During Command Sequence

The following detectable errors may occur when sending a command sequence to the ATA5577:

- Wrong number of field clocks between two gaps (i.e., not a valid 1 or 0 pulse stream)
- The number of bits received in the command sequence is incorrect

 Table 6-1.
 Bit Counts of Command Sequences

Command	Number of Bits
Write byte	16
Direct access	8
Read ID	2
Read upper bytes	2
Reset command	2

6.2 Errors Before/During Programming the EEPROM

If the command sequence was received successfully, the following errors may still prevent programming:

- The lock bits of the memory are already set
- If the memory is locked, programming is not possible. The ATA5575 will return to byte read mode, continuously transmitting the currently addressed byte.
- If a data verification error is detected after the programming of an executed data byte, the tag will stop modulation (modulation defeat) until a new command is transmitted.

Figure 6-1. ATA5575 Functional Diagram

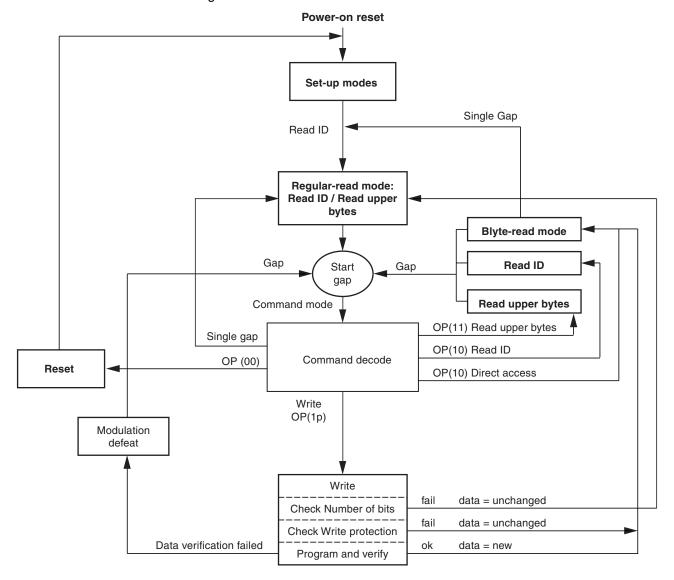
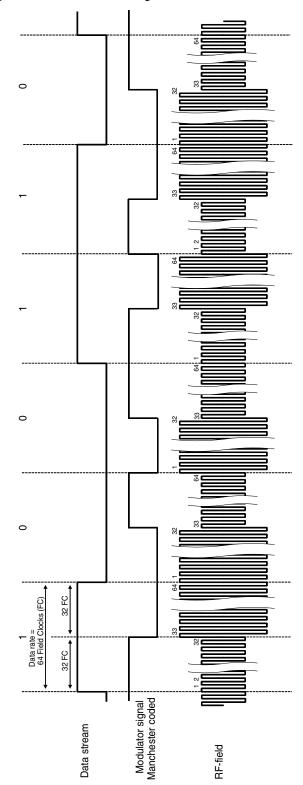




Figure 6-2. Example of Manchester Coding with Data Rate RF/64



7. Programming Examples

This section describes the data comparison for a typical application and provides programming examples.

A typical application is access control with Manchester coding, a data rate of RF/64 and a unique format data structure of 64 bit as described in Figure 7-1.

Figure 7-1. ATA5575M1: 64-bit User Data in Unique Format

_						•			
'1'	'1'	'1'	'1'	'1'	'1'	'1'	'1'	'1'	9 header bits
bit 1			Digit 0	D00	D01	D02	D03	PR0	
			Digit 1	D10	D11	D12	D13	PR1	Ф
by	te 0 to byte	e 3	Digit 2	D20	D21	D22	D23	PR2	even
			Digit 3	D30	D31	D32	D33	PR3	YOW
			Digit 4	D40	D41	D42	D43	PR4	row parity bit per digit
			Digit 5	D50	D51	D52	D53	PR5	ty b
			Digit 6	D60	D61	D62	D63	PR6	it pe
by	te 4 to byte	e 7	Digit 7	D70	D71	D72	D73	PR7	er <u>d</u> i
			Digit 8	D80	D81	D82	D83	PR8	gi÷
			Digit 9	D90	D91	D92	D93	PR9	
				PC0	PC1	PC2	PC3	'0'	_
				e/	en colum	nn parity b	its	bit 64	-

Table 7-1 on page 14 describes a programming of ATA5575M1 with unique format example data:

Digit 0, Digit 1, ..., Digit 9 = 0, 1, 2, 3, 4, 5, 6, 7, 8, 9





 Table 7-1.
 Programming ATA5575M1 with Unique Format Example Data

Base Station	ATA5575M1		
Field on for t = 5 ms	POR and regular read mode		
Command: 00	Reset		
Command: 10 0 0000 0110 10000	Programming byte 16 with '06h' (unique mode (Man RF/64, 64 bit), memory reprogrammable)		
Command: 10 0 1111 1111 00000	Programming byte 0 with 'FFh'		
Command: 10 0 1000 0000 00001	Programming byte 1 with '80h'		
Command: 10 0 0110 0101 00010	Programming byte 2 with '65h'		
Command: 10 0 0011 0010 00011	Programming byte 3 with '32h'		
Command: 10 0 0101 0100 00100	Programming byte 4 with '54h'		
Command: 10 0 1100 0111 00101	Programming byte 5 with 'C7h'		
Command: 10 0 1100 0110 00110	Programming byte 6 with 'C6h'		
Command: 10 0 0100 0010 00111	Programming byte 7 with '42h'		
Command: 10	Read ID		
Field on for t = 50 ms Read and verify data in unique format	Send data in unique format		
Command: 10 0 0110 1110 10000	Programming byte 16 with '6Eh' (memory locked, unique mode: Man RF/64, 64 bit)		
Command: 00	Reset		
Field on for t = 50 ms Read and verify data in unique format	Send data in unique format		

8. Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Parameters	Symbol	Value	Unit
Maximum DC current into Coil1/Coil2	I _{coil}	TBD	mA
Maximum AC current into Coil1/Coil2 f = 125 kHz	I _{coil p}	TBD	mA
Power dissipation (dice) (free-air condition, time of application: 1s)	P _{tot}	TBD	mW
Electrostatic discharge maximum to ANSI/ESD-STM5.1-2001 standard (HBM)	V _{max}	TBD	V
Operating ambient temperature range	T _{amb}	-40 to +85	°C
Storage temperature range (data retention reduced)	T _{stg}	-40 to +150	°C

9. Electrical Characteristics

 $T_{amb} = +25$ °C; $f_{coil} = 125$ kHz; unless otherwise specified

No.	Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit	Type*
1	RF frequency range		f _{RF}	100	125	150	kHz	
2.1	Supply current (without current consumed by the external LC tank circuit)	T _{amb} = 25°C ⁽¹⁾	I _{DD}		1.5	3	μА	Т
2.2		Read – full temperature range			2	5	μΑ	Q
2.3		Programming – full temperature range			25		μA	Q
3.1	Coil voltage (AC supply)	Read mode and write command ⁽²⁾	V _{coil pp}	6		V _{clamp}	V	Q
3.2		Program EEPROM ⁽²⁾		16		V _{clamp}	V	Q
4	Start-up time	$V_{\text{coil pp}} = 6V$	t _{startup}		1.1		ms	Q
5.1	Clomp	3 mA current into Coil1/2	V_{pp}	TBD	17	TBD	V	Т
5.2	Clamp	20 mA current into Coil1/2	V_{pp}	TBD	20	TBD	V	Т
6.1	Medulation parameters	3 mA current into Coil1/2 and modulation ON	V_{pp}	TBD	7	TBD	V	Q
6.2	Modulation parameters 6.2	20 mA current into Coil1/2 and modulation ON	V_{pp}	TBD	9	TBD	V	Т
6.3	Thermal stability		$V_{\text{mod lo}}/T_{\text{amb}}$		-1		mV/°C	Q

^{*)} Type means: T: directly or indirectly tested during production; Q: guaranteed based on initial product qualification data

Notes: 1. I_{DD} measurement setup: EEPROM programmed to 00 ... 000 (erase all); chip in modulation defeat.

- 2. Current into Coil1/Coil2 is limited to 10 mA.
- 3. Since the EEPROM performance is influenced by assembly processes, Atmel can not confirm the parameters for -DDW (tested die on unsawn wafer) delivery.
- 4. See Section 10. "Ordering Information" on page 17.





9. Electrical Characteristics (Continued)

 $T_{amb} = +25$ °C; $f_{coil} = 125$ kHz; unless otherwise specified

No.	Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit	Type*
7.1	Clock detection level	V _{coil pp} = 8V	V _{clkdet}	TBD	550	TBD	mV	T
7.2	Gap detection level	V _{coil pp} = 8V	V _{gapdet med}	TBD	550	TBD	mV	Т
8	Programming time	From last command gap to re-enter read mode (64 + 648 internal clocks)	T_{prog}	5	5.7	6	ms	Т
9	Endurance	Erase all / write all ⁽³⁾	n _{cycle}	100000			Cycles	Q
10.1		Top = $55^{\circ}C^{(3)}$	t _{retention}	10	20	50	Years	Q
10.2	Data retention	Top = $150^{\circ}C^{(3)}$	t _{retention}	96			hrs	Т
10.3		Top = 250°C ⁽³⁾	t _{retention}	24			hrs	Q
11.1	Posonance capacitor	Mask option ⁽⁴⁾	C	TBD	330	TBD	nE	т
11.2	Resonance capacitor	$V_{coil\ pp} = 1V$	C _r	TBD	250	TBD	pF	1

^{*)} Type means: T: directly or indirectly tested during production; Q: guaranteed based on initial product qualification data

Notes: 1. I_{DD} measurement setup: EEPROM programmed to 00 ... 000 (erase all); chip in modulation defeat.

- 2. Current into Coil1/Coil2 is limited to 10 mA.
- 3. Since the EEPROM performance is influenced by assembly processes, Atmel can not confirm the parameters for -DDW (tested die on unsawn wafer) delivery.
- 4. See Section 10. "Ordering Information" on page 17.

10. Ordering Information

ATA5575M1	ccc	-xxx	Package		Drawing
			DDB	6" sawn wafer on foil with ring, thickness 150 μm (approx. 6 mil)	Figure 11-4 on page 22
			DBB	$6"$ sawn wafer on foil with ring and gold bumps 25 $\mu m,$ thickness 150 μm (approx. 6 mil)	Figure 11-5 on page 23
			DBN	Die on sticky tape with gold bumps 25 μm, thickness 280 μm	Sticky Tape: 3M 7419 Figure 11-3 on page 21
			On-chip capa	city value in pF	
			250	(planned)	
			330		

Available Order Codes 10.1

ATA5575M1330-DDB

ATA5575M1330-DBB

New order codes will be created by customer request if order quantities exceed 250k pieces.

10.2 ATA5575M1 Configuration on Delivery

On delivery Atmel's production information is stored in EEPROM user data in unique format as described in Figure 7-1 on page 13.

Table 10-1. ATA5575M1: Configuration on Delivery

Byte	Address	Value	Comment
User data byte 0 to byte 7	0b 0 0000 to 0b 0 0111	Variable data	Unique ID in unique format
User data byte 8 to byte 15	0b 0 1000 to 0b 0 1111	Variable data	Unique ID in unique format (copy of byte 0 to byte 7)
Configuration (byte 16)	0b 1 0000	0x 06	Send unique format (Man RF/64, ID length = 64) with all digits '0'

The user data contains Atmel's lot and production information, which builds a unique ID numbering system as described in Table 10-2 on page 17.

Table 10-2. ATA5575M1: Meaning of the Digits in Delivery State

LSB first:

Denotation	Bit	Bitcount	Description
IC revision:	D00-D01	2	D00 is LSB of IC revision
Lot ID and wafer number:	D02-D61	24	D02 is LSB of lot ID & wafer number
DoW:	D62-D93	14	D62 is LSB of die on wafer



The lot ID and wafer number. (D02 to D62) contain the lot information and the wafer number. Including the die-on-wafer number, this information is used to build a unique ID numbering system, which means that each ATA5575M1 has a unique ID to distinguish from each other.

Atmel's lot ID has the following topology:

YQNNNN(#Wf)

- Y: alphanumeric 0, ..., 9
- · Q: character F, G, H and J
- NNNN: alphanumeric consecutive number 0, ..., 9999
- (#Wf): alphanumeric for wafer number 1, ..., 25

Lot ID and Wf No. is built in the following way:

- Transform Q = F, G, H, J into QQ = 0, ..., 3
- Transform wafer = 1, ..., 25 into WW = 0, ..., 24
- Lot ID and wafer number = $Y \times 1.000.000 + QQ \times 250.000 + NNNN \times 25 + WW$

This number is written binary into D02 to D61 with LSB first.

10.2.1 ATA5575M1 Example for Memory Content on Delivery

• ICR: '01b'

Lot number: 9F0164Wafer number: 12Die on wafer: 9.127

Lot ID and Wf No = $9 \times 1.000.000 + 0 \times 250.000 + 0164 \times 25 + 11 = 9.004.111$

Table 10-3. ATA5575M1: Example of Memory Content on Delivery

Byte#	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
Meaning	Header	Header / ICR / lot ID and wafer no.	Lot ID and wafer no.	Lot ID and wafer no.	Lot ID and wafer no.	Lot ID and wafer no./ DoW	DoW	DoW	Header	Header / ICR / Lot ID and wafer no.	Lot ID and wafer no.	Lot ID and wafer no.	Lot ID and wafer no.	Lot ID and wafer no./ DoW	DoW	DoW	Confi- guration
Value [hex]	FF	DF	11	95	12	F9	3C	60	FF	DF	11	95	12	F9	3C	60	06

11. Package Information

Figure 11-1. Pad Layout

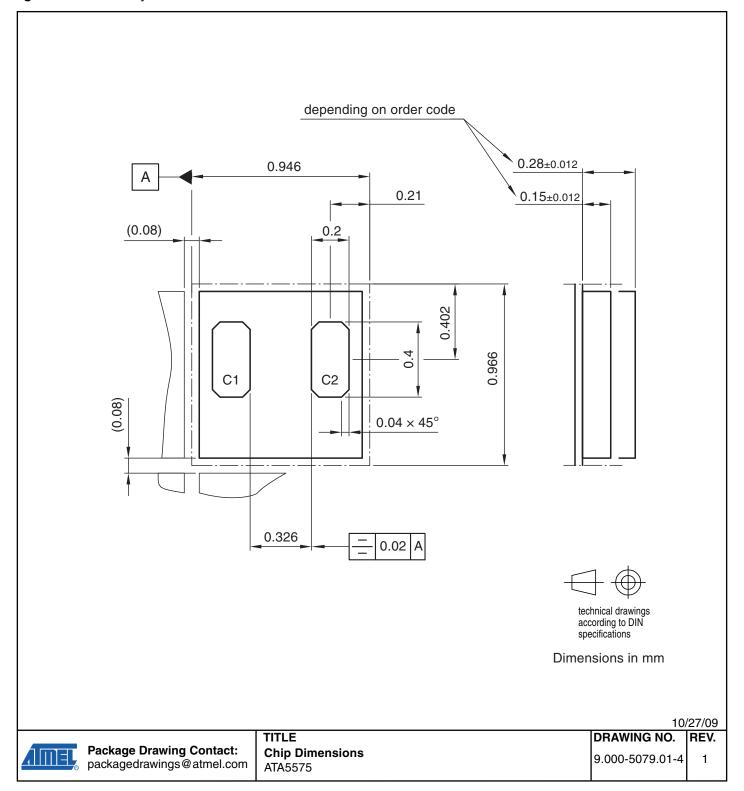






Figure 11-2. Pad Layout with Gold Bumps

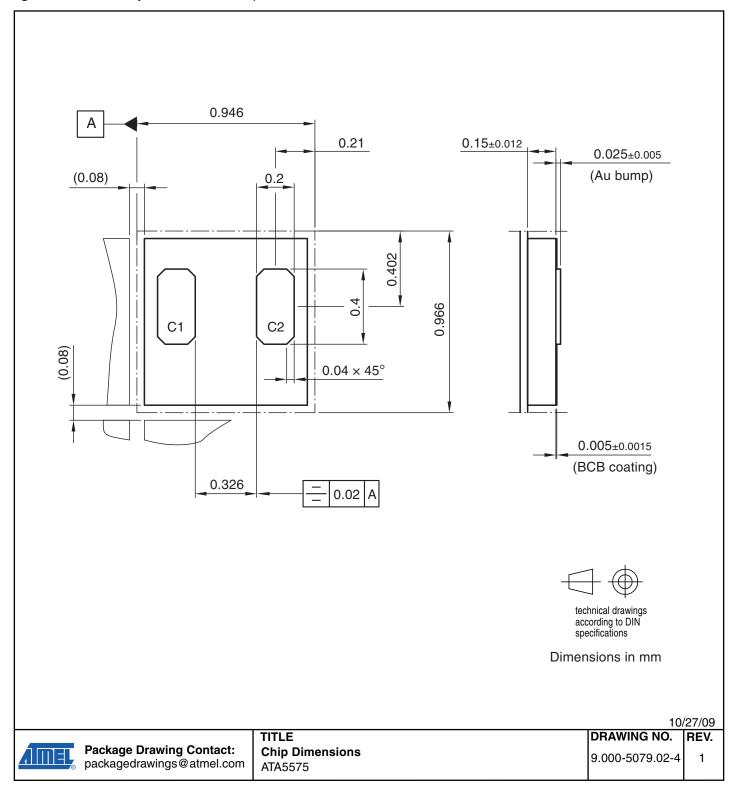


Figure 11-3. Pad Layout with Gold Bumps for Delivery on Sticky Tape

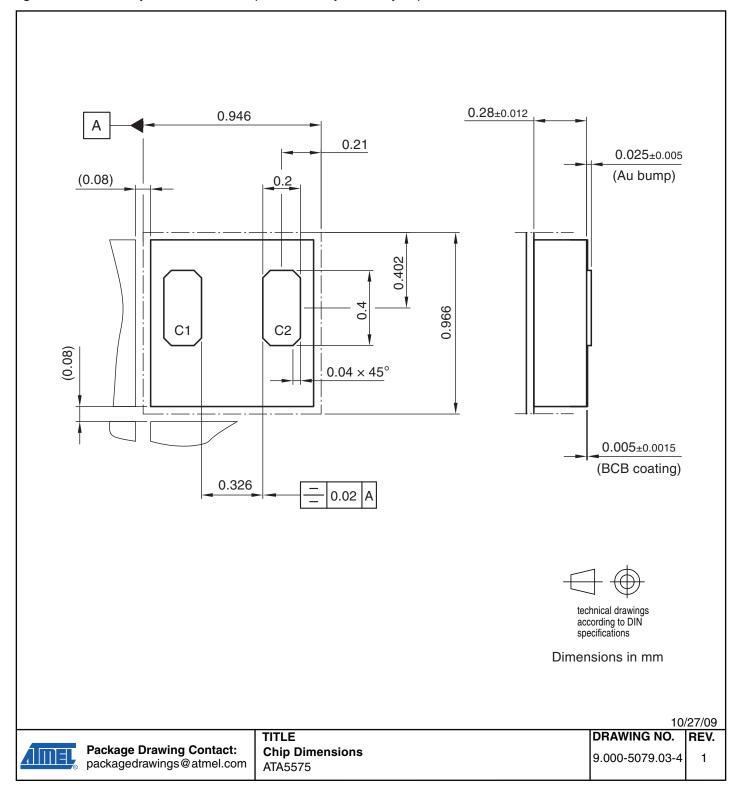




Figure 11-4. 6" Wafer on Foil with Ring

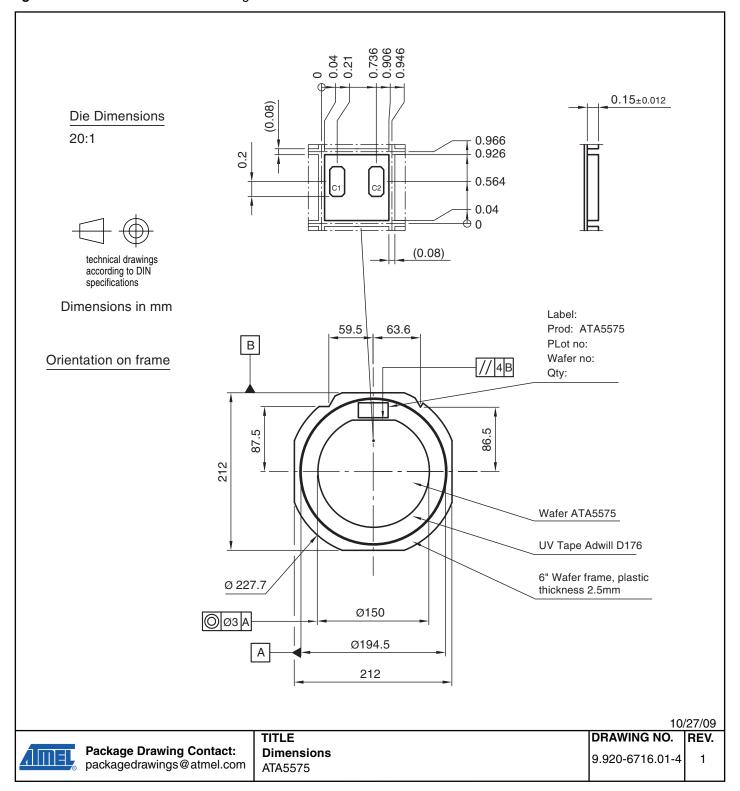
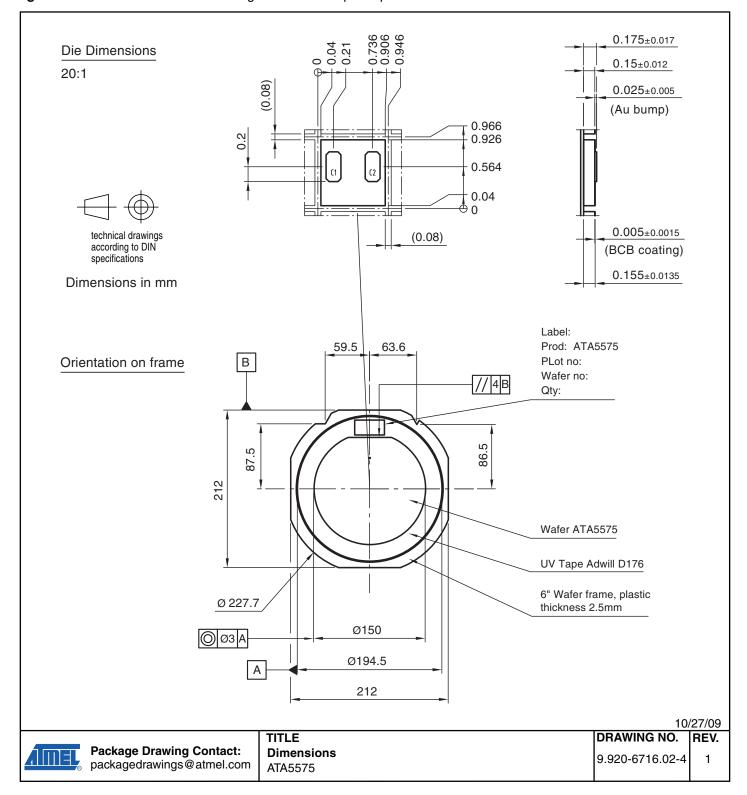


Figure 11-5. 6" Wafer on Foil with Ring and Gold Bumps 25 μm







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